## AMENDMENTS TO THE CLAIMS:

Please accept amendment(s) to the claims as follows:

- 1. (Currently Amended) A vertical PNP transistor and vertical NPN transistor comprising: an emitter region of the vertical PNP transistor including silicon and germanium; and an extrinsic base region of the vertical NPN transistor and an intrinsic base region of the vertical NPN transistor located in the same layer as the emitter region of the vertical PNP transistor.
- 2. (Original) The transistor of claim 1, wherein the germanium makes up no less than 10% of the silicon and germanium, and wherein the germanium makes up no more than 30% of the silicon and germanium.
- 3. (Original) The transistor of claim 1, wherein the silicon is a polysilicon.
- -4. - (Θriginal) The transistor of claim 1, wherein the transistor has a cutoff frequency greater than 10 GHz.
- \_5,\_ \_ (Original)-The transistor of claim 1, wherein the emitter region also includes carbon.
- 6. (Currently Amended) A vertical Vertical PNP and NPN transistor transistors comprising:
  a single layer of silicon that forms an emitter region of the PNP transistor, an extrinsic
  base region of the NPN transistor and an intrinsic base region of the NPN transistor.

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7.	(Currently Amende	d) The vertical PNP	and NPN	transistor	<del>transistors</del>	of claim 6,	wherein
an em	itter region of the PN	P transistor include	s silicon ar	nd german	ium.		

- 8. (Currently Amended) The vertical PNP and NPN transistor transistors of claim 7, wherein the germanium makes up no less than 10% of the silicon and germanium, and wherein the germanium makes up no more than 30% of the silicon and germanium.
- 9. (Currently Amended) The vertical PNP and NPN <u>transistor transistors</u> of claim 7, wherein the emitter region also includes carbon.
- 10. (Currently Amended) The vertical PNP and NPN transistor transistors of claim 7, wherein the silicon layer is polysilicon in the emitter region of the PNP transistor, and mono-crystal silicon in a portion of the extrinsic base region and mono-crystal silicon in the intrinsic base region of the NPN transistor.
- 11. (Currently Amended) The vertical PNP and NPN transistor transistors of claim 6, wherein the PNP transistor has a cutoff frequency greater than 10 GHz.

12-20. (Cancelled)

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